MOSFET – Power, P-Channel, High Side Load Switch with Level-Shift, SC-88

8 V, ±1.3 A

The NTJD1155L integrates a P and N–Channel MOSFET in a single package. This device is particularly suited for portable electronic equipment where low control signals, low battery voltages and high load currents are needed. The P–Channel device is specifically designed as a load switch using ON Semiconductor state–of–the–art trench technology. The N–Channel, with an external resistor (R1), functions as a level–shift to drive the P–Channel. The N–Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The NTJD1155L operates on supply lines from 1.8 to 8.0 V and can drive loads up to 1.3 A with 8.0 V applied to both $V_{\rm IN}$ and $V_{\rm ON/OFF}$.

Features

- Extremely Low R_{DS(on)} P-Channel Load Switch MOSFET
- Level Shift MOSFET is ESD Protected
- Low Profile, Small Footprint Package
- V_{IN} Range 1.8 to 8.0 V
- ON/OFF Range 1.5 to 8.0 V
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit | | | |
|-----------------------------------------------------|--------------------------------------|-----------------------|---------------------|------|----|--|
| Input Voltage (V _{DSS} , P-Ch | V_{IN} | 8.0 | V | | | |
| ON/OFF Voltage (V _{GS} , N- | ·Ch) | | V _{ON/OFF} | 8.0 | V | |
| Continuous Load Current | Steady | T _A = 25°C | ΙL | ±1.3 | Α | |
| (Note 1) | State | T _A = 85°C | | ±0.9 | | |
| Power Dissipation | Steady | T _A = 25°C | P_{D} | 0.40 | W | |
| (Note 1) | State | T _A = 85°C | | 0.20 | | |
| Pulsed Load Current | I_{LM} | ±3.9 | Α | | | |
| Operating Junction and St | T _J , T _{STG} | –55 to 150 | ô | | | |
| Source Current (Body Dio | I _S | -0.4 | Α | | | |
| Lead Temperature for Solo (1/8" from case for 10 s) | dering Pur | poses | TL | 260 | °C | |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---------------------------------------------|-----------------|-----|------|
| Junction-to-Ambient - Steady State (Note 1) | $R_{\theta JA}$ | 320 | °C/W |
| Junction-to-Foot - Steady State (Note 1) | $R_{\theta JF}$ | 220 | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

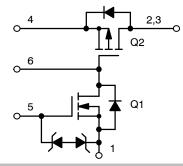


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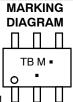
| V _{(BR)DSS} R _{DS(on)} TYP | | I _D MAX |
|----------------------------------------------|-----------------|--------------------|
| | 130 mΩ @ -4.5 V | |
| 8.0 V | 170 mΩ @ –2.5 V | ±1.3 A |
| | 260 mΩ @ -1.8 V | |

SIMPLIFIED SCHEMATIC





SC-88 (SOT-363) CASE 419B STYLE 30

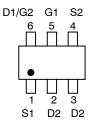


TB = Device Code M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

| Device | Package | Shipping [†] | | |
|-------------------------------|--------------------|-----------------------|--|--|
| NTJD1155LT1G, NTJD1155LT2G | SC-88 (Pb-Free) | 3000/Tape & Reel | | |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

| 1. | Surface-mounted on FR4 board using 1 inch sq pad size (Cu area = 1.127 in sq [1 oz] including traces). |
|----|--------------------------------------------------------------------------------------------------------|
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ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Test Condition | | Min | Тур | Max | Unit |
|--------------------------------------|----------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------|------|------|------|------|
| OFF CHARACTERISTICS | | | | • | | | • |
| Q2 Drain-to-Source Breakdown Voltage | V _{IN} | V _{GS2} = 0 V, I _{D2} = | = 250 μΑ | -8.0 | | | V |
| Forward Leakage Current | I _{FL} | V _{GS1} = 0 V, | T _J = 25°C | | | 1.0 | μΑ |
| | | $V_{DS2} = -8.0 \text{ V}$ | T _J = 125°C | | | 10 | |
| Q1 Gate-to-Source Leakage Current | I _{GSS} | V _{DS1} = 0 V, V _{GS1} | _I = ±8.0 V | | | ±100 | nA |
| Q1 Diode Forward On-Voltage | V_{SD} | $I_S = -0.4 \text{ A}, V_{GS}$ | _{S1} = 0 V | | -0.8 | -1.1 | V |
| ON CHARACTERISTICS | | | | | | | |
| ON/OFF Voltage | V _{ON/OFF} | | | 1.5 | | 8.0 | V |
| Q1 Gate Threshold Voltage | V _{GS1(th)} | V _{GS1} = V _{DS1} , I _D = 250 μA | | 0.4 | | 1.0 | V |
| Input Voltage | V _{IN} | $V_{GS1} = V_{DS1}, I_D = 250 \mu A$ | | 1.8 | | 8.0 | V |
| Q2 Drain-to-Source On Resistance | R _{DS(on)} | $V_{ON/OFF} = 1.5 \text{ V}$ $V_{IN} = 4.5 \text{ V}$ $I_{L} = 1.2 \text{ A}$ $V_{IN} = 2.5 \text{ V}$ $I_{L} = 1.0 \text{ A}$ $V_{IN} = 1.8 \text{ V}$ $I_{L} = 0.7 \text{ A}$ | | | 130 | 175 | mΩ |
| | | | | | 170 | 220 | |
| | | | | | 260 | 320 | |
| Load Current | ال | $V_{DROP} \le 0.2 \text{ V}, V_{IN} = 5.0 \text{ V}, \\ V_{ON/OFF} = 1.5 \text{ V}$ $V_{DROP} \le 0.3 \text{ V}, V_{IN} = 2.5 \text{ V}, \\ V_{ON/OFF} = 1.5 \text{ V}$ | | 1.0 | | | Α |
| | | | | 1.0 | | | |

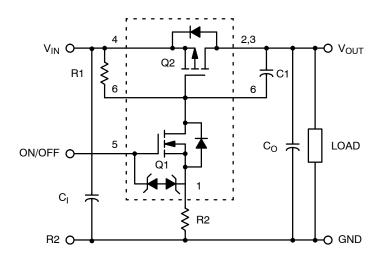
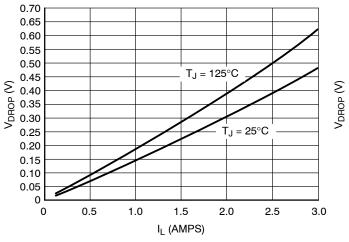


Figure 1. Load Switch Application

| Components | Description | Values |
|---------------------------------|----------------------------------|-------------------------------------------|
| R1 | Pullup Resistor | Typical 10 k Ω to 1.0 M Ω^* |
| R2 | Optional Slew-Rate Control | Typical 0 to 100 kΩ* |
| C _O , C _I | Output Capacitance | Usually < 1.0 μF |
| C1 | Optional In-Rush Current Control | Typical ≤ 1000 pF |

^{*}Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

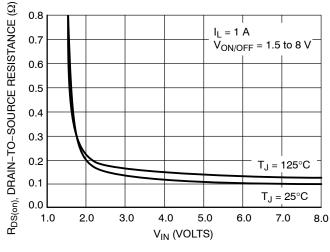
TYPICAL PERFORMANCE CURVES ($T_J = 25^{\circ}C$ unless otherwise noted)



0.50 0.45 0.40 0.35 $T_J = 125^{\circ}C$ 0.30 0.25 0.20 $T_J = 25^{\circ}C$ 0.15 0.10 0.05 0.5 1.0 1.5 2.0 2.5 3.0 0 I_L (AMPS)

Figure 2. V_{drop} vs. $I_L @ V_{in}$ = 2.5 V

Figure 3. V_{drop} vs. $I_L @ V_{in} = 4.5 \text{ V}$



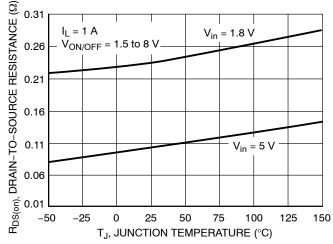
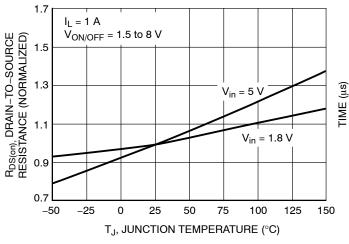


Figure 4. On-Resistance vs. Input Voltage

Figure 5. On–Resistance Variation with Temperature





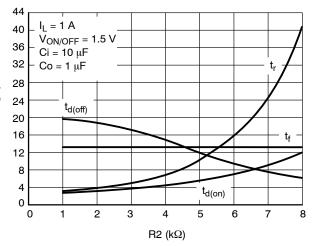


Figure 7. Switching Variation R2 @ V_{in} = 4.5 V, R1 = 20 k Ω

$\textbf{TYPICAL PERFORMANCE CURVES} \ (T_J = 25^{\circ}\text{C unless otherwise noted})$

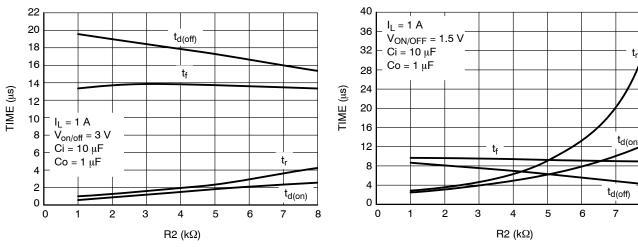


Figure 8. Switching Variation R2 @ V_{in} = 4.5 V, R1 = 20 $k\Omega$

Figure 9. Switching Variation R2 @ V_{in} = 2.5 V, R1 = 20 k Ω

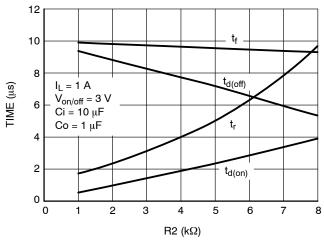


Figure 10. Switching Variation R2 @ V_{in} = 2.5 V, R1 = 20 $k\Omega$

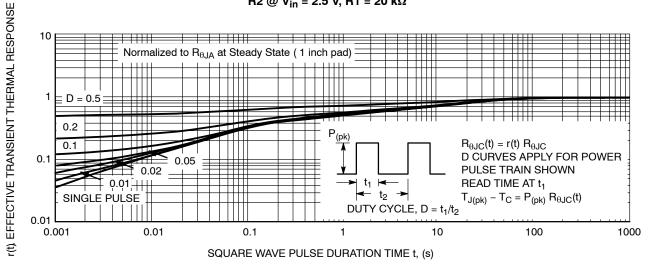
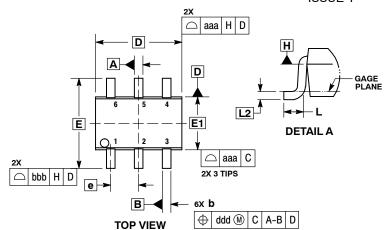


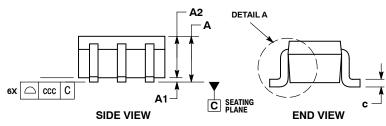
Figure 11. FET Thermal Response

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02 **ISSUE Y**





NOTES

ddd

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- DIMENSIONING AND TOLERANGUING PER ASMIE Y 14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.

- THE PLASTIC BODY AND DATUM H.

 DATUMS A AND B ARE DETERMINED AT DATUM H.

 DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE
 LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.

 DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION.

 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN

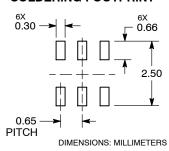
 EXCESS OF DIMENSION B AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER

| HADIOS OF THE FOOT. | | | | | | | | |
|---------------------|-------------|-----------|------|--------|-------|-------|--|--|
| | MILLIMETERS | | | INCHES | | | | |
| DIM | MIN | I NOM MAX | | MIN | NOM | MAX | | |
| Α | | | 1.10 | | | 0.043 | | |
| A1 | 0.00 | | 0.10 | 0.000 | | 0.004 | | |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 | | |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | | |
| С | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 | | |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 | | |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 | | |
| F1 | 1 15 | 1 25 | 1.35 | 0.045 | 0.049 | 0.053 | | |

| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | | |
|-----|----------------|----------|------|-------|-----------|-------|--|--|
| С | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 | | |
| D | 1.80 2.00 | | 2.20 | 0.070 | 0.078 | 0.086 | | |
| Е | 2.00 2.10 2.1 | | 2.20 | 0.078 | 0.082 | 0.086 | | |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 | | |
| е | | 0.65 BSC | | | 0.026 BSC | | | |
| L | 0.26 0.36 0.46 | | 0.46 | 0.010 | 0.014 | 0.018 | | |
| L2 | | 0.15 BSC | | | 0.006 BSC | | | |
| aaa | 0.15 | | | 0.006 | | | | |
| bbb | 0.30 | | | 0.012 | | | | |
| ccc | 0.10 | | | | 0.004 | | | |

0.10

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 SOURCE 2 GATE 1 DRAIN 1

0.004

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